TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74HCT4053AF,TC74HCT4053AFN,TC74HCT4053AFT

Triple 2-Channel Analog Multiplexer/Demultiplexer

The TC74HCT4053A are high speed CMOS ANALOG MULTIPLEXER/DEMULTIPLEXER fabricated with silicon gate C^2MOS technology. They achieve the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

This device may be used as a level converter for interfacing TTL or NMOS to High Speed CMOS. This inputs are compatible with TTL, NMOS and CMOS output voltage levels.

The TC74HCT4053A has a 2 channel \times 3 configuration.

The digital signal to the control terminal turns "ON" the corresponding switch of each channel a large amplitude signal ($V_{\rm CC}-V_{\rm EE}$) can then be switched by the small logical amplitude ($V_{\rm CC}-{\rm GND}$) control signal.

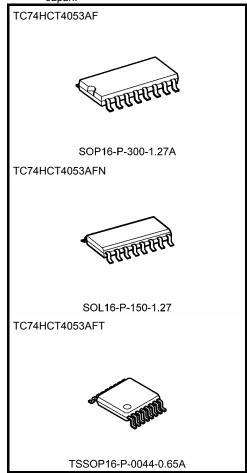
For example, in the case of $V_{CC}=5$ V, GND=0 V, $V_{EE}=-5$ V, signals between -5 V and +5 V can be switched from the logical circuit with a single power supply of 5 V. As the ON-resistance of each switch is low, they can be connected to circuits with low input impedance.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

Features

- High speed: tpd = 30 ns (typ.) at $V_{CC} = 5 \text{ V}$ $V_{EE} = 0 \text{ V}$
- Low power dissipation: $I_{CC} = 4 \mu A \text{ (max)}$ at $T_{a} = 25 \text{°C}$
- Compatible with TTL output: $V_{IH} = 2.0 \text{ V (min)}$ $V_{IL} = 0.8 \text{ V (max)}$
- Wide interfacing ability: LSTTL, NMOS, CMOS
- Low ON resistance: $RON = 50 \Omega$ (typ.) at VCC VEE = 9 V
- High noise immunity: THD = 0.02% (typ.) at $V_{CC} V_{EE} = 9 \text{ V}$
- Pin and function compatible with 4053B

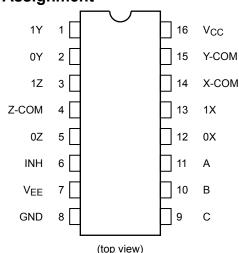
Note: xxxFN (JEDEC SOP) is not available in Japan.



Weight

SOP16-P-300-1.27A : 0.18 g (typ.) SOL16-P-150-1.27 : 0.13 g (typ.) TSSOP16-P-0044-0.65A : 0.06 g (typ.)

Pin Assignment

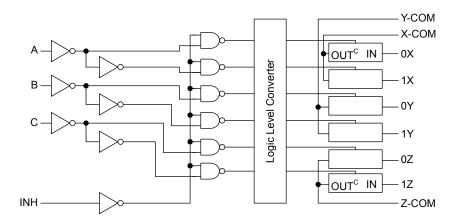


Truth Table

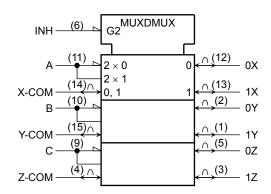
	Contro	"ON" Channel		
Inhibit	С	В	Α	HCT4053A
L	L	L	L	0X, 0Y, 0Z
L	┙	┙	Н	1X, 0Y, 0Z
L	┙	Н	┙	0X, 1Y, 0Z
L	┙	Н	Н	1X, 1Y, 0Z
L	Н	┙	┙	0X, 0Y, 1Z
L	Н	L	Н	1X, 0Y, 1Z
L	Н	Н	L	0X, 1Y, 1Z
L	Н	Н	Н	1X, 1Y, 1Z
Н	X	X	X	NONE

X: Don't care

System Diagram



IEC Logic Symbol



2



Absolute Maximum Ratings (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	–0.5 to 13	V
Supply voltage range	V _{CC} – V _{EE}	−0.5 to 13	V
Control input voltage	V _{IN}	-0.5 to V _{CC} + 0.5	V
Switch I/O voltage	V _{I/O}	$V_{\mbox{\footnotesize EE}}$ – 0.5 to $V_{\mbox{\footnotesize CC}}$ + 0.5	V
Control input diode current	I _{ICK}	±20	mA
I/O diode current	l _{IOK}	±20	mA
Switch through current	ΙΤ	±25	mA
DC V _{CC} or ground current	Icc	±50	mA
Power dissipation	PD	180	mW
Storage temperature	T _{stg}	-65 to 150	°C

Note: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Operating Ranges (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	4.5 to 12	V
Supply voltage range	V _{EE}	-7.5 to 0	٧
Supply voltage range	V _{CC} – V _{EE}	4.5 to 12	٧
Control input voltage	V _{IN}	0 to V _{CC}	٧
Switch I/O voltage	V _{I/O}	V _{EE} to V _{CC}	٧
Operating temperature	T _{opr}	−40 to 85	°C
Control input rise and fall time	t _r , t _f	0 to 500	ns

Note: The operating ranges must be maintained to ensure the normal operation of the device.

Unused control inputs must be tied to either VCC or GND.



Electrical Characteristics

DC Characteristics

Characteristics	Symbol	Test Condition		Ta = 25°C			Ta = -40 to 85°C		Unit	
	,		V _{EE} (V)	V _{CC} (V)	Min	Тур.	Max	Min	Max	
High-level control input voltage	V _{IHC}			4.5 to 5.5 9.0	2.0 2.5	_	_	2.0 2.5	_	٧
Low-level control input voltage	V _{ILC}			4.5 to 5.5 9.0		_	0.8 0.8	_	0.8 0.8	٧
ON resistance	Ron	$\begin{aligned} V_{IN} &= V_{ILC} \text{ or } V_{IHC} \\ V_{I/O} &= V_{CC} \text{ to } V_{EE} \\ I_{I/O} &\leq 2 \text{ mA} \end{aligned}$	GND -4.5 -5.5 GND	4.5 4.5 5.5 9.0		85 55 50 55	180 120 110 120	_ _ _ _	225 150 140 150	Ω
	0.1	$\begin{aligned} &V_{IN} = V_{ILC} \text{ or } V_{IHC} \\ &V_{I/O} = V_{CC} \text{ or } V_{EE} \\ &I_{I/O} \leq 2 \text{ mA} \end{aligned}$	GND -4.5 -5.5 GND	4.5 4.5 5.5 9.0		70 50 45 50	150 100 90 100		190 125 115 125	
Difference of ON resistance between switches	ΔR _{ON}	$\begin{aligned} V_{IN} &= V_{ILC} \text{ or } V_{IHC} \\ V_{I/O} &= V_{CC} \text{ to } V_{EE} \\ I_{I/O} &\leq 2 \text{ mA} \end{aligned}$	GND -4.5 -5.5	4.5 4.5 5.5		10 5 5	30 12 11	_ 	35 15 14	Ω
Input/output leakage current (switch OFF)	loff	$V_{OS} = V_{CC}$ or GND $V_{IS} = GND$ or V_{CC} $V_{IN} = V_{ILC}$ or V_{IHC}	GND -5.5	5.5 5.5			±60 ±100		±600 ±1000	nA
Switch input leakage current (switch ON)	I _{IZ}	$V_{OS} = V_{CC}$ or GND $V_{IN} = V_{ILC}$ or V_{IHC}	GND -5.5	5.5 5.5			±60 ±100	_	±600 ±1000	nA
Control input current	I _{IN}	$V_{IN} = V_{CC}$ or GND	GND	5.5	_	_	±0.1	_	±1.0	μА
Quiescent supply current	Icc	V _{IN} = V _{CC} or GND	GND -5.5	5.5 5.5	_	_ _	4.0 8.0	_	40.0 80.0	μА
	I _C	Per input: V _{IN} = 0.5 V or 2.4 V Other input: V _{CC} or GND	GND	5.5	_	_	2.0	_	2.9	mA

4



AC Characteristics (C_L = 50 pF, Input $t_r = t_f = 6$ ns, GND = 0 V)

Characteristics Symb		Test Condition			Ta = 25°C			Ta = -40 to 85°C		Unit
	.,		V _{EE} (V)	V _{CC} (V)	Min	Тур.	Max	Min	Max	J
Phase difference between input and output	φΙ/О		GND GND GND	4.5 5.5 9.0	_ _ _	6 5 4	12 11 —	_ _ _	15 14 —	ns
Output enable time	^t pZL t _{pZH}	(Note 1)	GND GND GND	4.5 5.5 9.0		33 26 17	50 45 —		63 57 —	ns
Output disable time	^t pLZ t _{pHZ}	(Note 1)	GND GND GND	4.5 5.5 9.0		45 37 26	65 59 —	_ _ _	81 73 —	ns
Control input capacitance	C _{in}		_	_	_	5	10	_	10	pF
COMMON terminal capacitance	C _{IS}		-5.0	5.0	_	11	20	_	20	pF
SWITCH terminal capacitance	C _{OS}		-5.0	5.0	_	7	15	_	15	pF
Feedthrough capacitance	C _{IOS}		-5.0	5.0	_	0.75	2	_	2	pF
Power dissipation capacitance	C _{PD}	(Note 2)	GND	5.0	_	67	_	_	_	pF

Note 1 $R_L = 1 k\Omega$

Note 2: C_{PD} is defined as the value of the internal equivalent capacitance of IC which is calculated from the operating current consumption without load.

5

Average operating current can be obtained by the equation:

$$I_{CC} (opr) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$



Analog Switch Characteristics (GND = 0 V, Ta = 25°C) (Note 1)

Characteristics	Characteristics Symbol Test Condition					Тур.	Unit
Characteristics	Onaracteristics Oyinboi		V _{EE} (V)	V _{CC} (V)	Onit		
Sine wave distortion (T.H.D)		$R_L = 10 \text{ k}\Omega$ $C_L = 50 \text{ pF}$ $f_{IN} = 1 \text{ kHz}$	$V_{IN} = 8.0 V_{p-p}$ $V_{IN} = 11.0 V_{p-p}$	-4.5 -5.5	4.5 5.5	0.020 0.019	%
		Adjust f _{IN} voltage to obtain 0dBm at V _{OS}	(Note 2)	-4.5	4.5	190	
Frequency response	f _{MAX}	Increase f _{IN} frequency until dB meter reads –3dB	(Note 3)	-4.5	4.5	150	MHz
(switch ON)	INAX	$R_L = 50 \Omega$, $C_L = 10 pF$	(Note 2)	-5.5	5.5	200	
		f _{IN} = 1 MHz, Sine wave	(Note 3)	-5.5	5.5	180	
Feed through attenuation (switch OFF)		Vin is centered at $(V_{CC} - V_{EE})/2$ Adjust input for 0dBm $R_L = 600 \ \Omega, \ C_L = 50 \ pF$ $f_{IN} = 1 \ MHz$, Sine wave		-4.5 -5.5	4.5 5.5	–50 –50	dB
Crosstalk (control input to signal output)		$R_L = 600 \ \Omega$, $C_L = 50 \ pF$ $f_{IN} = 1 \ MHz$, Square wave $(t_r = t_f = 6 \ ns)$		-4.5 -5.5	4.5 5.5	140 180	mV
Crosstalk (between any switches)		Adjust V_{IN} to obtain 0dBm at input R _L = 600 Ω , C _L = 50 pF f _{IN} = 1 MHz, Sine wave		-4.5 -5.5	4.5 5.5	-50 -50	dB
a, amonos,		$R_L = 50 \Omega$, $C_L = 15 pF$ $f_{IN} = 100 \text{ kHz}$, $V_{SWITCH} = 1 V_{RMS}$		-4.5	4.5	-90	dB

6

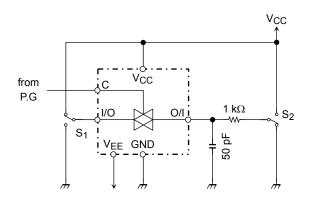
Note 1: These characteristics are determined by design of devices.

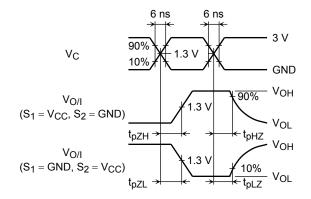
Note 2: Input COMMON terminal, and measured at SWITCH terminal.

Note 3: Input SWITCH terminal, and measured at COMMON terminal.

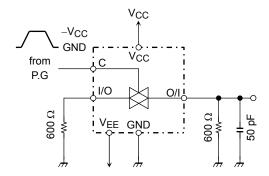
Switching Characteristics Test Circuits

1. t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

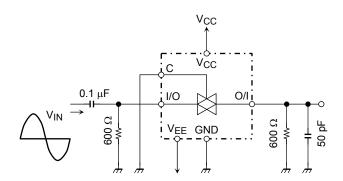




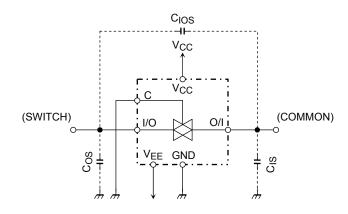
2. Cross Talk (control input – switch output) $f_{IN} = 1$ MHz duty = 50% $t_r = t_f = 6$ ns



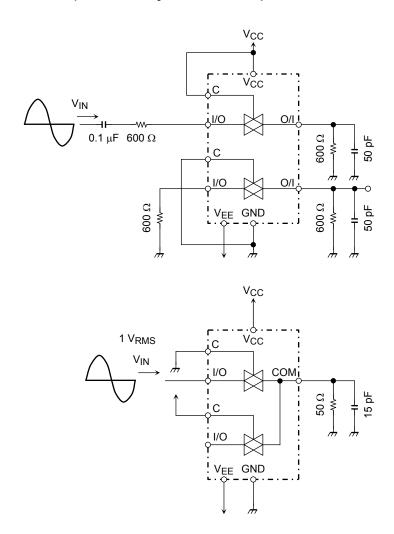
3. Feedthrough Attenuation



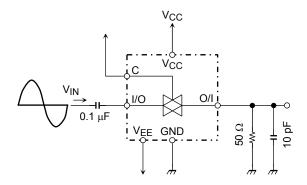
4. C_{IOS} , C_{IS} , C_{OS}



5. Cross Talk (between any two switches)



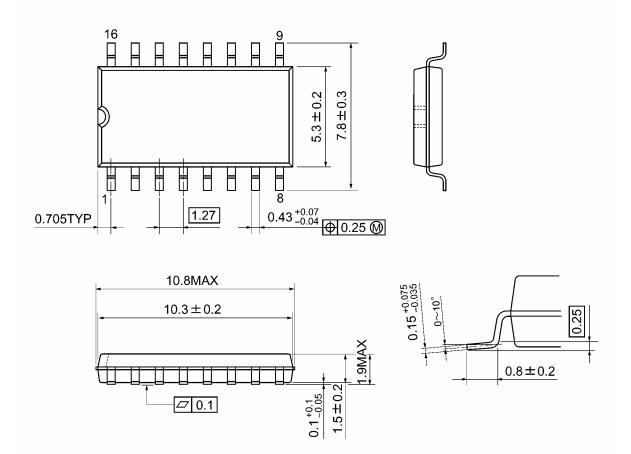
6. Frequency Response (switch ON)



8

Package Dimensions

SOP16-P-300-1.27A Unit: mm

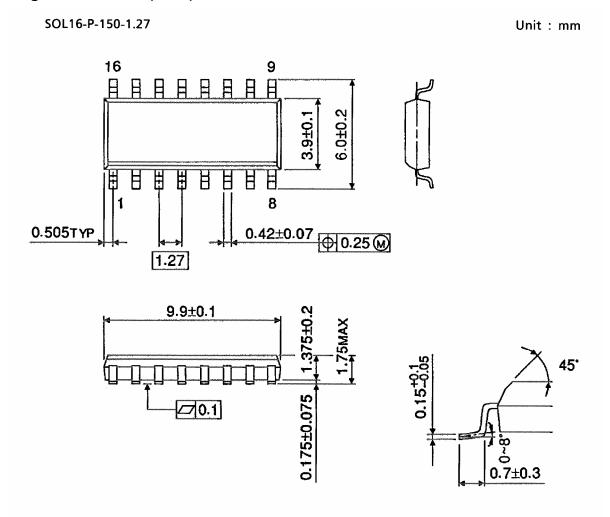


9

Weight: 0.18 g (typ.)



Package Dimensions (Note)



10

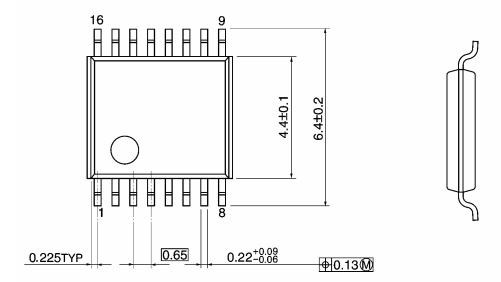
Note: This package is not available in Japan.

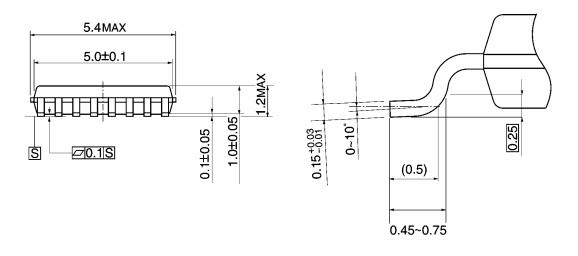
Weight: 0.13 g (typ.)

Package Dimensions

TSSOP16-P-0044-0.65A

Unit: mm





Weight: 0.06 g (typ.)

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Handbook" etc.

20070701-EN GENERAL

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